

SANYO	No.4540	3SK248
		N-Channel Enhancement MOS Silicon FET Muting/Switching Applications

Features

- MOS FET with a back gate terminal.
- Enhancement type.
- Small ON resistance.
- Small-sized package permitting 3SK248-applied sets to be made smaller and slimmer.

Absolute Maximum Ratings at Ta = 25°C

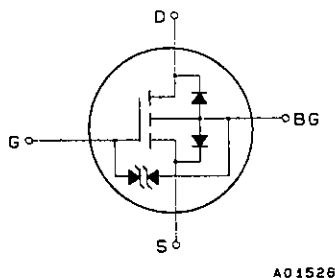
			unit
Drain-to-Source Voltage	V _{DSS}	10	V
Gate-to-Source Voltage	V _{GSS}	±10	V
Drain Current	I _D	100	mA
Allowable Power Dissipation	P _D	200	mW
Channel Temperature	T _{ch}	125	°C
Storage Temperature	T _{stg}	-55 to +125	°C

Electrical Characteristics at Ta = 25°C

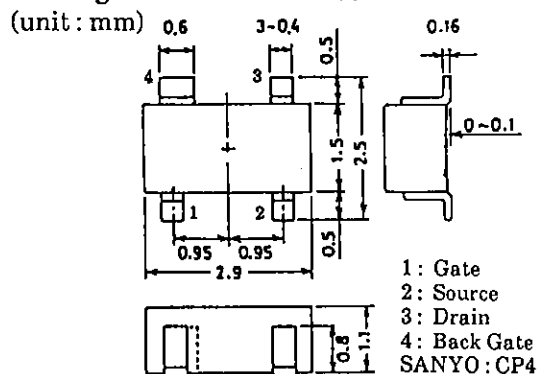
			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = 10 μA, V _{GS} = 0V	10			V
G-S Breakdown Voltage	V _{GSS}	I _G = ±10 μA, V _{DS} = 0V	±10			V
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = ±8V, V _{DS} = 0V		±0.01	±50	nA
Cutoff Voltage	V _{GS(off)}	V _{DS} = 5V, I _D = 100 μA	0.3		1.5	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 5V, V _{GS} = 0V			1	μA
Forward Transfer Admittance	Y _{fs}	V _{DS} = 5V, I _D = 50mA, f = 1kHz		80		mS
Input Capacitance	C _{iss}	V _{DS} = 5V, V _{GS} = 0V, f = 1MHz		50		pF
Output Capacitance	C _{oss}	V _{DS} = 5V, V _{GS} = 0V, f = 1MHz		10		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = 5V, V _{GS} = 0V, f = 1MHz		5		pF
Static Drain-to-Source on state Resistance	R _{DS(on)1}	V _{GS} = 5V, I _D = 50mA		5	7	Ω
	R _{DS(on)2}	V _{GS} = 2.5V, I _D = 15mA		7	12	Ω

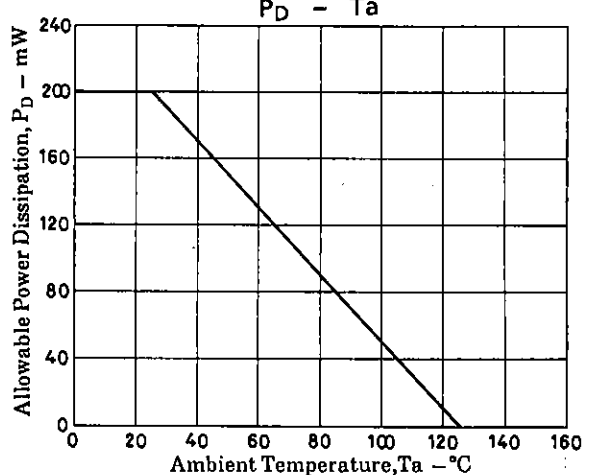
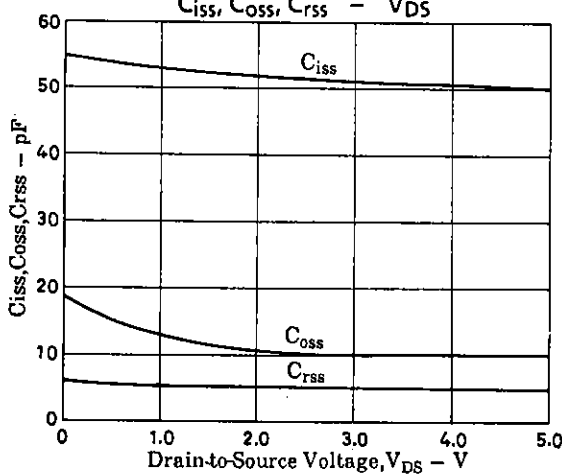
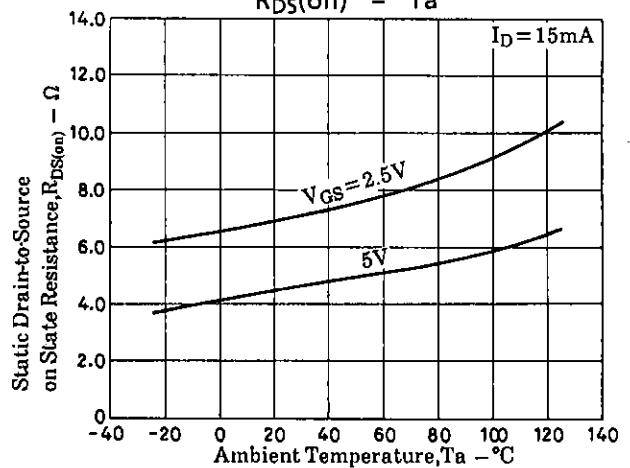
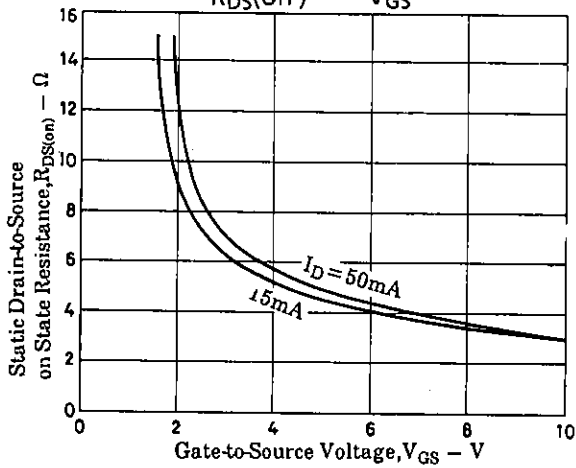
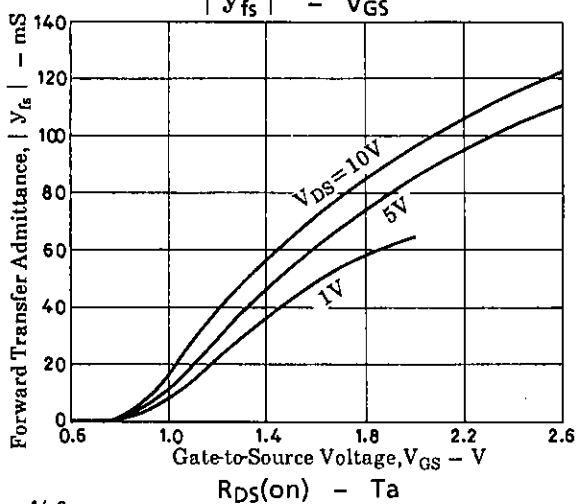
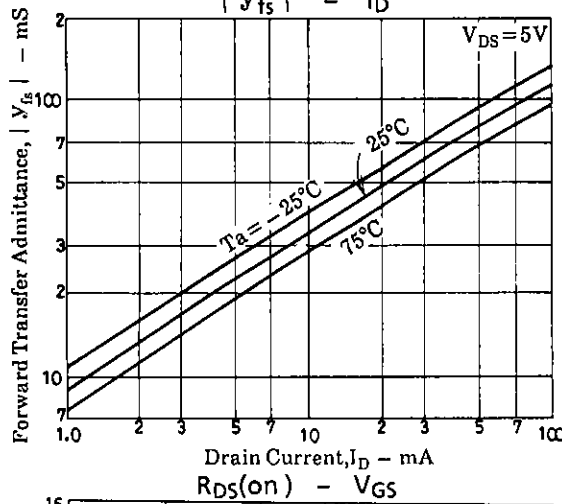
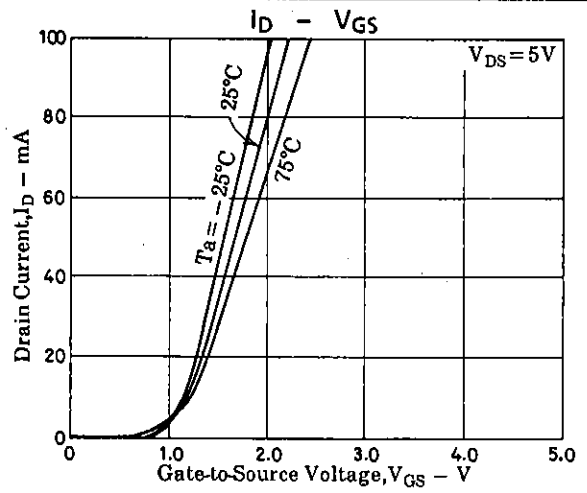
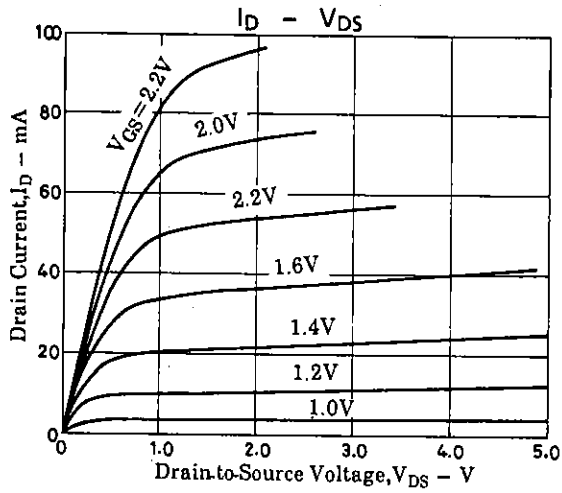
Marking : NJ

Electrical Connection



Package Dimensions 2100A





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